



- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

### Product Summary

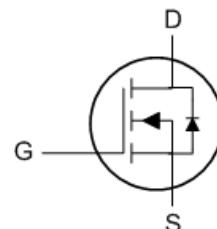
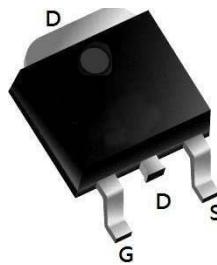
| BVDSS | RDS(ON) | ID  |
|-------|---------|-----|
| 60V   | 5.3mΩ   | 80A |

### Description

The XXW80N06 is the high performance complementary N-ch MOSFETs with high cell density, which provide excellent RDS(ON) and gate charge for most of the synchronous buck converter applications.

The XXW80N06 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

### TO252 Pin Configuration



### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

| Symbol         | Parameter                                       |                           | Max.        | Units                     |
|----------------|---|---------------------------|-------------|---------------------------|
| $V_{DSS}$      | Drain-Source Voltage                            |                           | 60          | V                         |
| $V_{GSS}$      | Gate-Source Voltage                             |                           | $\pm 25$    | V                         |
| $I_D$          | Continuous Drain Current                        | $T_C = 25^\circ\text{C}$  | 80          | A                         |
|                |   | $T_C = 100^\circ\text{C}$ | 52          | A                         |
| $I_{DM}$       | Pulsed Drain Current <sup>note1</sup>           |                           | 320         | A                         |
| EAS            | Single Pulsed Avalanche Energy <sup>note2</sup> |                           | 169         | mJ                        |
| $P_D$          | Power Dissipation                               | $T_C = 25^\circ\text{C}$  | 108         | W                         |
| $R_{eJC}$      | Thermal Resistance, Junction to Case            |                           | 1.4         | $^\circ\text{C}/\text{W}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range         |                           | -55 to +175 | °C                        |

**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

| Symbol  | Parameter   | Test Condition  | Min. | Typ. | Max.      | Units            |
|---|---|---|------|------|-----------|------------------|
| <b>Off Characteristic</b>                                     |   |   |      |      |           |                  |
| $V_{(\text{BR})\text{DSS}}$                                   | Drain-Source Breakdown Voltage                            | $V_{GS}=0\text{V}$ , $I_D=250\mu\text{A}$   | 60   | -    | -         | V                |
| $I_{\text{DSS}}$  | Zero Gate Voltage Drain Current                           | $V_{DS}=60\text{V}$ , $V_{GS}=0\text{V}$ ,  | -    | -    | 1.0       | $\mu\text{A}$    |
| $I_{GSS}$   | Gate to Body Leakage Current                              | $V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$                                      | -    | -    | $\pm 100$ | nA               |
| <b>On Characteristics</b>                                     |   |   |      |      |           |                  |
| $V_{GS(\text{th})}$   | Gate Threshold Voltage                                    | $V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$  | 2    | 3    | 4         | V                |
| $R_{DS(\text{on})}$   | Static Drain-Source on-Resistance<br><small>note3</small> | $V_{GS}=10\text{V}$ , $I_D=30\text{A}$  | -    | 5.3  | 7         | $\text{m}\Omega$ |
| <b>Dynamic Characteristics</b>                                |   |   |      |      |           |                  |
| $C_{iss}$   | Input Capacitance   | $V_{DS}=30\text{V}$ , $V_{GS}=0\text{V}$ ,<br>$f=1.0\text{MHz}$                   | -    | 4136 | -         | pF               |
| $C_{oss}$   | Output Capacitance  |   | -    | 286  | -         | pF               |
| $C_{rss}$   | Reverse Transfer Capacitance                              |   | -    | 257  | -         | pF               |
| $Q_g$   | Total Gate Charge   | $V_{DS}=30\text{V}$ , $I_D=30\text{A}$ ,<br>$V_{GS}=10\text{V}$                   | -    | 90   | -         | nC               |
| $Q_{gs}$  | Gate-Source Charge  |   | -    | 9    | -         | nC               |
| $Q_{gd}$  | Gate-Drain("Miller") Charge                               |   | -    | 18   | -         | nC               |
| <b>Switching Characteristics</b>                              |   |   |      |      |           |                  |
| $t_{d(on)}$   | Turn-on Delay Time  | $V_{DS}=30\text{V}$ , $I_D=30\text{A}$ ,<br>$R_G=1.8\Omega$ , $V_{GS}=10\text{V}$ | -    | 9    | -         | ns               |
| $t_r$   | Turn-on Rise Time   |   | -    | 7    | -         | ns               |
| $t_{d(off)}$  | Turn-off Delay Time                                       |   | -    | 40   | -         | ns               |
| $t_f$   | Turn-off Fall Time  |   | -    | 15   | -         | ns               |
| <b>Drain-Source Diode Characteristics and Maximum Ratings</b> |   |   |      |      |           |                  |
| $I_S$   | Maximum Continuous Drain to Source Diode Forward Current  | -   | -    | 80   | -         | A                |
| $I_{SM}$  | Maximum Pulsed Drain to Source Diode Forward Current      | -   | -    | 320  | -         | A                |
| $V_{SD}$  | Drain to Source Diode Forward Voltage                     | $V_{GS}=0\text{V}$ , $I_S=30\text{A}$   | -    | -    | 1.2       | V                |
| $trr$   | Body Diode Reverse Recovery Time                          | $I_F=30\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$                                | -    | 33   | -         | ns               |
| $Qrr$   | Body Diode Reverse Recovery Charge                        |   | -    | 46   | -         | nC               |

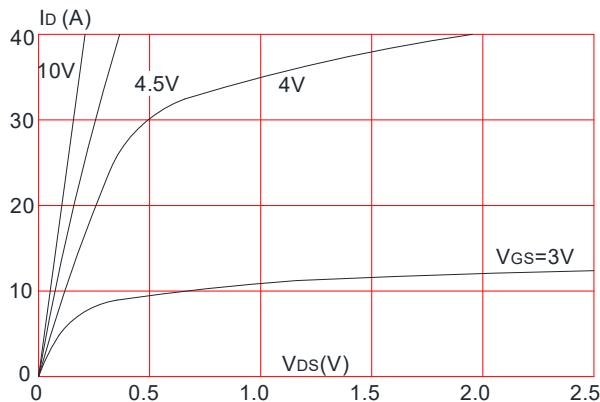
Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition :  $T_J=25^\circ\text{C}$ ,  $V_{DD}=30\text{V}$ ,  $V_G=10\text{V}$ ,  $L=0.5\text{mH}$ ,  $R_g=25\Omega$ ,  $I_{AS}=26\text{A}$

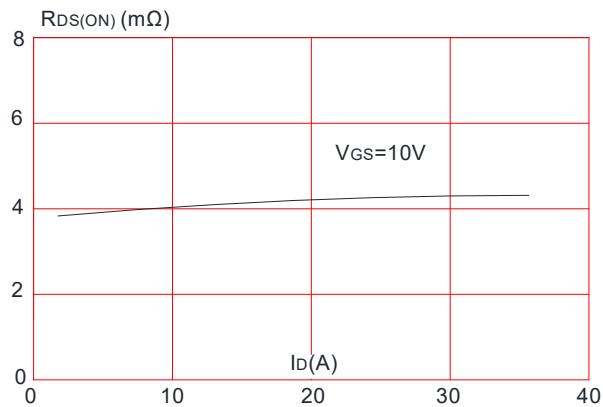
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$ , Duty Cycle $\leq 0.5\%$

## Typical Performance Characteristics

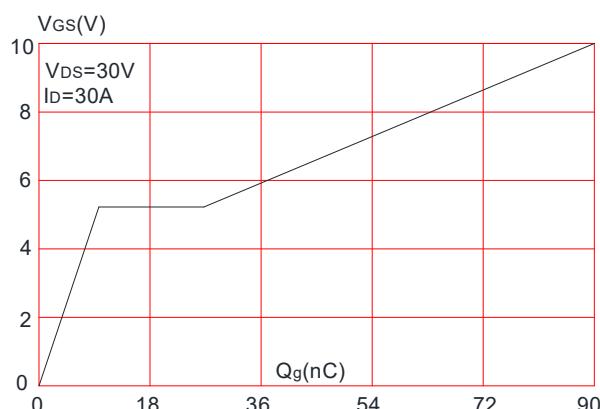
**Figure 1:** Output Characteristics



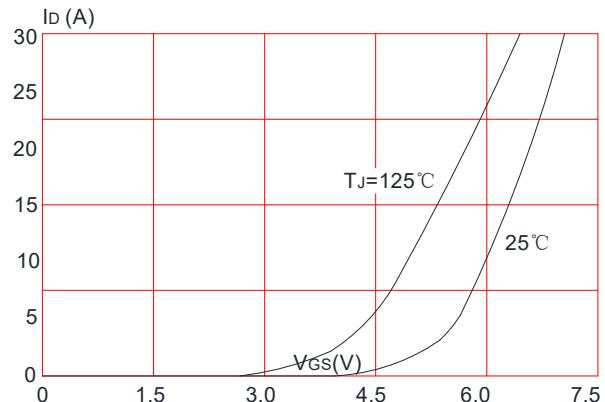
**Figure 3:** On-resistance vs. Drain Current



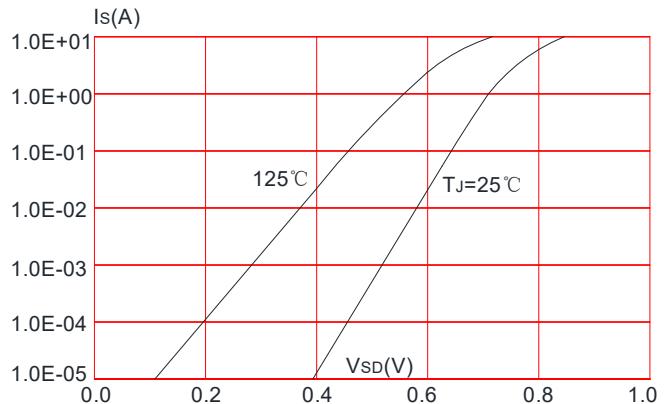
**Figure 5:** Gate Charge Characteristics



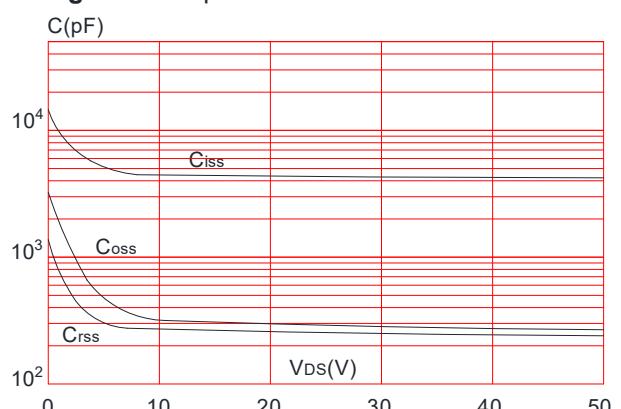
**Figure 2:** Typical Transfer Characteristics



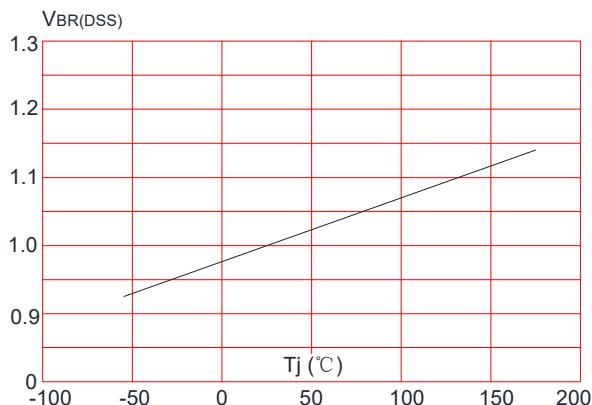
**Figure 4:** Body Diode Characteristics



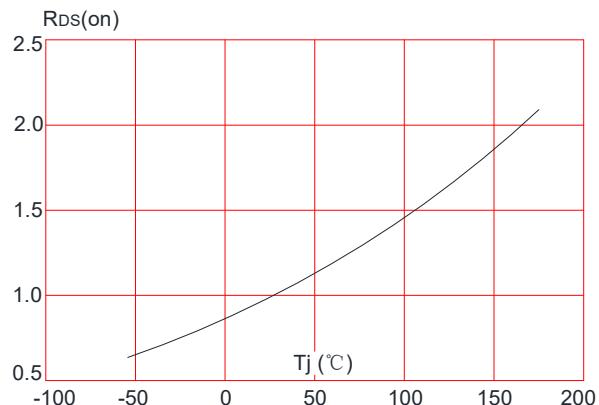
**Figure 6:** Capacitance Characteristics



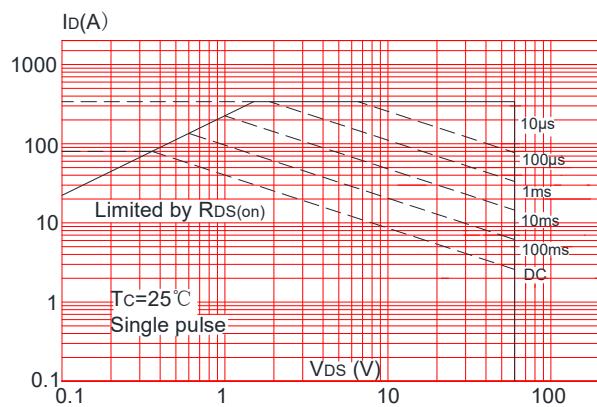
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



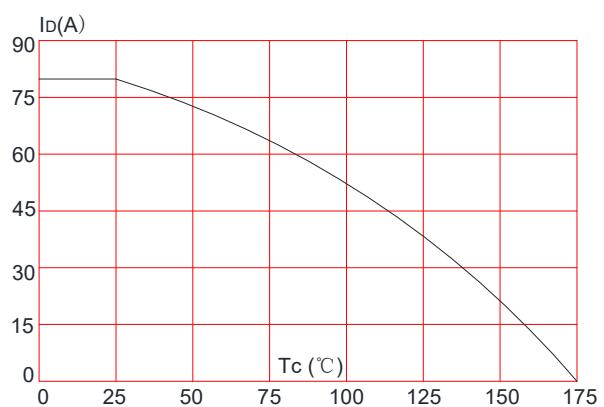
**Figure 8:** Normalized on Resistance vs. Junction Temperature



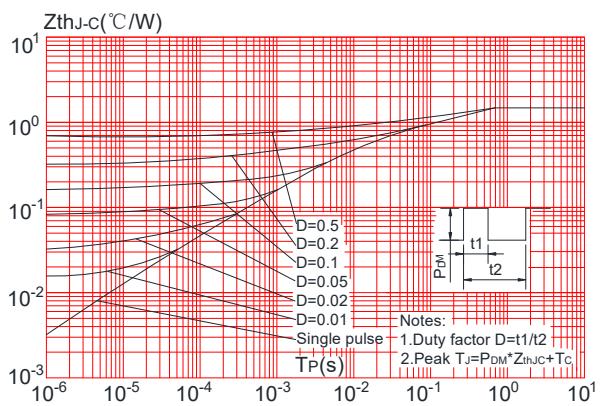
**Figure 9:** Maximum Safe Operating Area



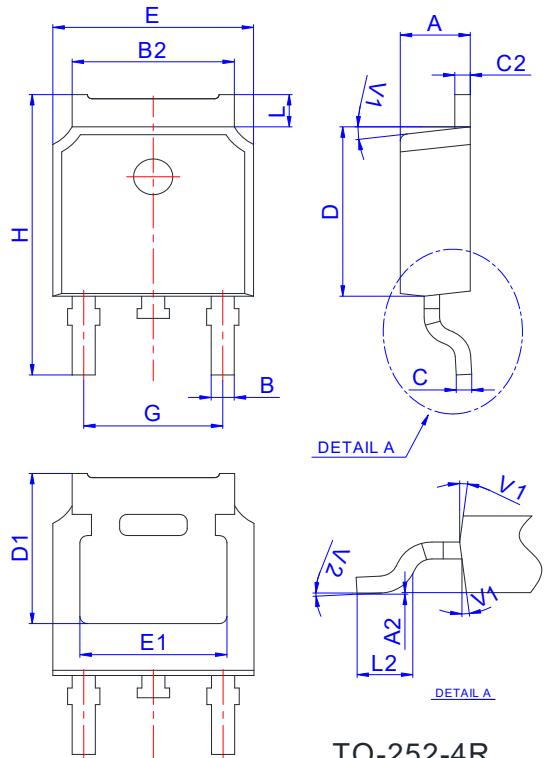
**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case



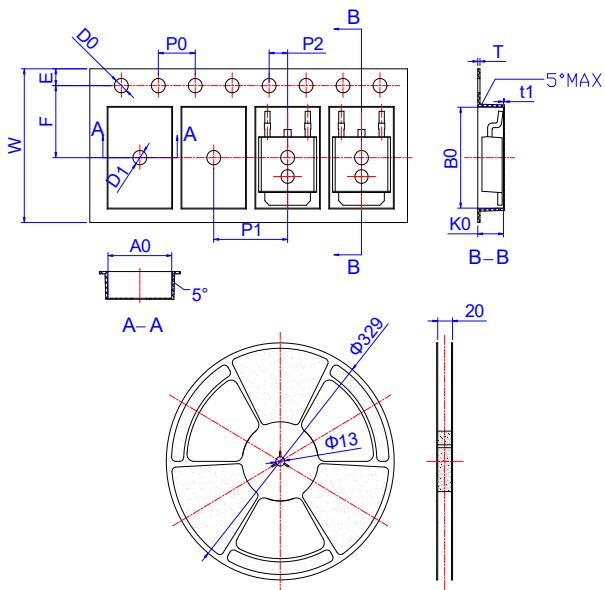
## Package Mechanical Data-TO-252-4R



TO-252-4R

| Ref. | Dimensions  |      |       |          |      |       |
|------|-------------|------|-------|----------|------|-------|
|      | Millimeters |      |       | Inches   |      |       |
|      | Min.        | Typ. | Max.  | Min.     | Typ. | Max.  |
| A    | 2.10        |      | 2.50  | 0.083    |      | 0.098 |
| A2   | 0           |      | 0.10  | 0        |      | 0.004 |
| B    | 0.66        |      | 0.86  | 0.026    |      | 0.034 |
| B2   | 5.18        |      | 5.48  | 0.202    |      | 0.216 |
| C    | 0.40        |      | 0.60  | 0.016    |      | 0.024 |
| C2   | 0.44        |      | 0.58  | 0.017    |      | 0.023 |
| D    | 5.90        |      | 6.30  | 0.232    |      | 0.248 |
| D1   | 5.30REF     |      |       | 0.209REF |      |       |
| E    | 6.40        |      | 6.80  | 0.252    |      | 0.268 |
| E1   | 4.63        |      |       | 0.182    |      |       |
| G    | 4.47        |      | 4.67  | 0.176    |      | 0.184 |
| H    | 9.50        |      | 10.70 | 0.374    |      | 0.421 |
| L    | 1.09        |      | 1.21  | 0.043    |      | 0.048 |
| L2   | 1.35        |      | 1.65  | 0.053    |      | 0.065 |
| V1   |             | 7°   |       |          | 7°   |       |
| V2   | 0°          |      | 6°    | 0°       |      | 6°    |

## Reel Specification-TO-252-4R



| Ref. | Dimensions  |       |       |        |       |       |
|------|-------------|-------|-------|--------|-------|-------|
|      | Millimeters |       |       | Inches |       |       |
|      | Min.        | Typ.  | Max.  | Min.   | Typ.  | Max.  |
| W    | 15.90       | 16.00 | 16.10 | 0.626  | 0.630 | 0.634 |
| E    | 1.65        | 1.75  | 1.85  | 0.065  | 0.069 | 0.073 |
| F    | 7.40        | 7.50  | 7.60  | 0.291  | 0.295 | 0.299 |
| D0   | 1.40        | 1.50  | 1.60  | 0.055  | 0.059 | 0.063 |
| D1   | 1.40        | 1.50  | 1.60  | 0.055  | 0.059 | 0.063 |
| P0   | 3.90        | 4.00  | 4.10  | 0.154  | 0.157 | 0.161 |
| P1   | 7.90        | 8.00  | 8.10  | 0.311  | 0.315 | 0.319 |
| P2   | 1.90        | 2.00  | 2.10  | 0.075  | 0.079 | 0.083 |
| A0   | 6.85        | 6.90  | 7.00  | 0.270  | 0.271 | 0.276 |
| B0   | 10.45       | 10.50 | 10.60 | 0.411  | 0.413 | 0.417 |
| K0   | 2.68        | 2.78  | 2.88  | 0.105  | 0.109 | 0.113 |
| T    | 0.24        |       | 0.27  | 0.009  |       | 0.011 |
| t1   | 0.10        |       |       | 0.004  |       |       |
| 10P0 | 39.80       | 40.00 | 40.20 | 1.567  | 1.575 | 1.583 |